



## Electronic structure of CeCo<sub>2</sub> thin films studied by X-ray absorption spectroscopy

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### Abstract

We present an X-ray absorption near-edge structure (XANES) study at Ce L<sub>3</sub>-, and Co K-edges of CeCo<sub>2</sub> thin films with the thickness varying from 30 to 140 nm. Ce L<sub>3</sub>-edge spectra exhibit the mixed valence nature and the tetravalent contribution increases with the thickness of CeCo<sub>2</sub>. The variation in the spectral intensity observed at Co K-edge threshold indicates that there is a change in 3d occupancy and also in 3d–4f–5d hybridization. This study shows the effect of surface to bulk ratio and how it influences the charge transfer between Ce and Co ions and hence the electronic structure of CeCo<sub>2</sub> thin films.

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*Keywords:* XANES; Mixed valence; Surface; Thin film

### 1. Introduction

CeCo<sub>2</sub> is a superconducting compound with transition temperature  $T_c$  of 1 K [1]. It has been considered that Ce in CeCo<sub>2</sub> is in an intermediate valence state due to the collapsed volume and both Ce and Co are essentially nonmagnetic [1,2]. The intriguing behavior of 4f electrons in rare-earth compounds is that it possesses both localized and band-like characters. It becomes clear that the electronic and magnetic properties of materials in nanoscale are different from the bulk even though their chemical composition being the same. Recent study on CeAl<sub>2</sub>, it has demonstrated that the bulk CeAl<sub>2</sub> exhibits magnetic ordering while CeAl<sub>2</sub> nanoparticles show nonmagnetic nature [3]. This phenomenon has been attributed to the effect of surface to bulk ratio [4]. On the contrary, CeCo<sub>2</sub> exhibits the opposite behavior [2]. It would be of interest to investigate how bulk to surface effect influences the electronic structure on CeCo<sub>2</sub>. X-ray absorption near edge

structure (XANES) has been a favored experimental tool to study the core level changes and understand the electronic structure with thin films of different thickness.

### 2. Experimental

The CeCo<sub>2</sub> thin films of thickness 30, 40, 70, 110 and 140 nm were prepared by flash evaporation of bulk CeCo<sub>2</sub> ingot onto a liquid nitrogen cold trap in a 0.1 Torr of high purity helium and the thickness of these films were monitored by a quartz crystal oscillator during the evaporation process. Details are given elsewhere [3]. X-ray absorption measurements were carried out at beamline 17C at the National Synchrotron Radiation Research Center (NSRRC), Taiwan, in fluorescence mode at room temperature.

### 3. Results and discussions

Fig. 1(a) shows XANES spectra at Ce L<sub>3</sub>-edges of CeCo<sub>2</sub> thin films. The unoccupied Ce 5d orbital produces two

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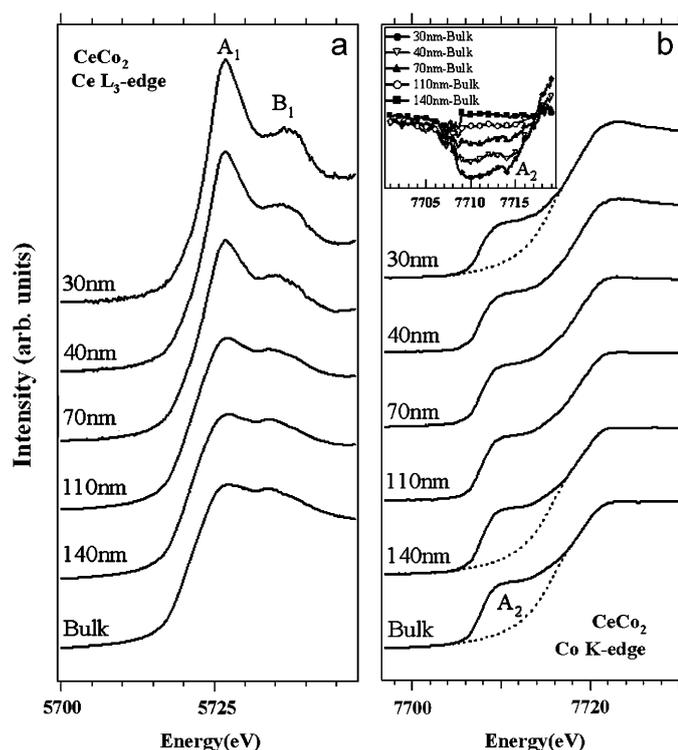


Fig. 1. XANES spectra for bulk  $\text{CeCo}_2$  and thin films at (a)  $\text{Ce L}_3$ -edge and (b)  $\text{Co K}$ -edge. Inset in (b) is obtained after subtracting the spectrum of bulk  $\text{CeCo}_2$ .

prominent  $\text{L}_3$  white lines, marked as  $A_1$  and  $B_1$  which are ascribed, respectively, to  $2p^*4f^1(5d6s)^4$  and  $2p^*4f^0(5d6s)^5$  final states, corresponding to  $\text{Ce}^{3+}$  and  $\text{Ce}^{4+}$  states [5]. The  $2p^*$  denotes a hole in  $2p$  level. As evident from the figure, there is a clear spectral evolution indicating the valence change with thickness. The enhancement of  $4f^1$  states in very thin films implies the increased  $4f$  electron occupancy of  $\text{Ce}$  atoms.

XANES spectra at  $\text{Co K}$ -edge are presented in Fig. 1(b). The absorption feature  $A_2$  at  $\sim 7110$  eV primarily reflects

the density of empty  $3d$  states through the  $s$ - $p$ - $d$  rehybridization [6]. The systematic reduction of the feature  $A_2$  with thickness shows the electronic perturbation of the density of state resulting from the surface to bulk ratio. The inset of Fig. 1(b) obtained after subtracting the bulk spectra, shows that the hybridization between conduction states of  $\text{Ce } 4f5d$  and  $\text{Co } 3d$  states increases with film thickness. It is also noted that the unoccupied  $3d$  states increase as film thickness decrease. By comparing the results from  $\text{Ce L}_3$ - and  $\text{Co K}$ -edges, the charge transfer between  $\text{Ce}$  and  $\text{Co}$  may be the consequence of the valence change driven by the different surface to bulk ratio.

#### 4. Conclusions

The XANES study at  $\text{Ce L}_3$ -edge revealed the mixed valence nature of  $\text{Ce}$  ions and the contribution of  $\text{Ce}^{4+}$  is reducing as thickness decreases [5]. On the other hand, the XANES at  $\text{Co K}$ -edge provides evidence that the  $3d$  occupancy varies with film thickness [7]. These results suggest that the valence change is due to the charge transfer driven by the surface to bulk ratio effect.

#### Acknowledgments

This work was supported by the US Department of Energy, under contract no. DE-AC02-05CH1123 and the National Science Council of the Republic of China through grant no. NSC 95-2112-M-032-008.

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